

Refine Search

Your wildcard search against 10000 terms has yielded the results below.

Your result set for the last L# is incomplete.

The probable cause is use of unlimited truncation. Revise your search strategy to use limited truncation.

Search Results -

Terms	Documents
L3 same test\$	23

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L4

Refine Search

Recall Text

Clear

Interrupt

Search History

DATE: Thursday, December 23, 2004 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<u>L4</u>	L3 same test\$	23	<u>L4</u>
<u>L3</u>	L1 near2 device	693	<u>L3</u>
<u>L2</u>	"same adj1 type"	0	<u>L2</u>
<u>L1</u>	(common or identical) adj1 type	28960	<u>L1</u>

END OF SEARCH HISTORY

[First Hit](#) [Fwd Refs](#)[Previous Doc](#)[Next Doc](#)[Go to Doc#](#)

Generate Collection

Print

L4: Entry 15 of 23

File: USPT

Jul 10, 1973

DOCUMENT-IDENTIFIER: US 3745460 A

TITLE: METHOD AND APPARATUS FOR DETERMINING THE THERMAL INTERNAL RESISTANCE IN SEMICONDUCTORS OF THE SAME TYPE

Brief Summary Text (12):

According to the method of the present invention, the internal thermal resistance of identical types of semiconductor devices can be measured or correlated in a very short time, i.e., in 50 to 500 ms, depending on the type of the device. Due to the short time required for this test, semiconductor devices of a series can be individually tested in succession. However, a plurality of semiconductor devices of a series can be successively checked in groups or at random if the appropriate number of testing devices and measuring sensors are provided. An arrangement constructed according to an embodiment of the present invention with a thermoelement usable as a temperature sensor for accomplishing the method of the invention for individually testing the semiconductor devices will be explained in detail in the description of the invention provided below.

[Previous Doc](#)[Next Doc](#)[Go to Doc#](#)